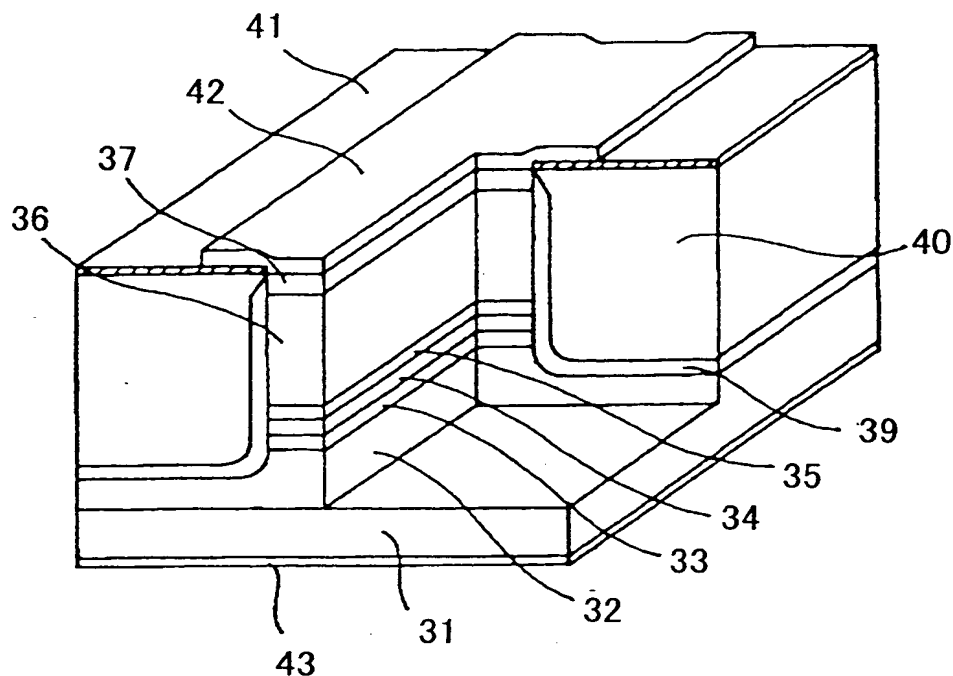


FIG. 19



- 31: n-InP substrate
- 32: Se-doped n-InP cladding layer
- 33: Nondoped InGaAsP guide layer
- 34: Nondoped InGaAlAs/InAlAs strained MQW (multiple quantum well) photoabsorption layer
- 35: Nondoped InGaAsP guide layer
- 36: Zn-doped p-InP cladding layer
- 37: Zn-doped InGaAs contact layer
- 39: Ru-doped InP layer
- 40: Fe-doped InP layer
- 41: SiO<sub>2</sub> passivation film
- 42: p-electrode
- 43: n-electrode